

ABSTRACT OF THE DISCLOSURE

A resist pattern is formed on a film to be processed using a lithography technique. The line width of the resist pattern is narrowed using a slimming technique. Thereafter, the pattern of a first film to be processed is formed in the space that has been widened by slimming, utilizing the phenomenon in which anisotropic etching under a reduced pressure accelerates the etching rate in the vicinity of the side of the line of the pattern compared to other areas. An underlying second film to be processed is etched using the first film to be processed as a mask. Thereby the pattern of the second film to be processed that has a pitch $1/2$ the lithography pattern is formed.

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